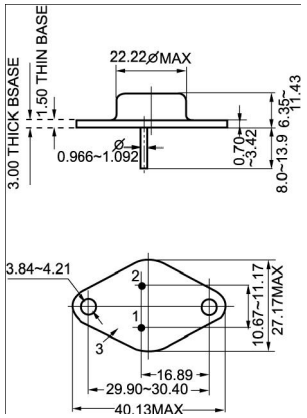
NPN Silicon Power Darlington Transistors

2N6576

FEATURES:

1.High Gain Darlington Performance
2. Built-in Diode Protection for Reverse Polarity Protection
3. Can Be Driven from Low-Level Logic
4. Popular Voltage Range

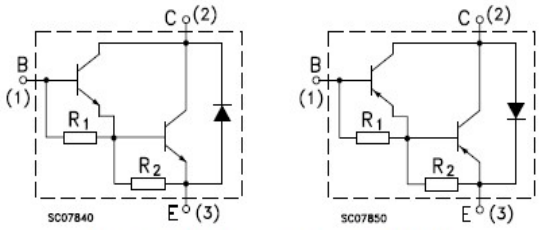


TO-3

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	15	A
Base Current	I_B	0.5	A
Total Dissipation at	P_{tot}	120	W
Max. Operating Junction Temperature	T_j	120	°C
Storage Temperature	T_{stg}	-55~150	°C

INTERNAL SCHEMATIC DIAGRAM



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I_{CEO}	V_{CE} = 60V, I_B = 0	—	—	1.0	mA
Collector Cut-off Current	I_{CBO}	V_{CB} = 60V, I_E = 0	—	—	0.5	mA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 5.0V, I_C = 0	—	—	2.0	mA
Collector-Emitter Sustaining Voltage	V_{CEO}	I_C = 30mA, I_B = 0	60	—	—	V
DC Current Gain	$h_{FE(1)}$	V_{CE} = 3.0V, I_C = 4.0A	2000	—	—	
	$h_{FE(2)}$	V_{CE} = 3.0V, I_C = 10A	500	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 10A, I_B = 100mA	—	—	2.5	V
		I_C = 15A, I_B = 150mA	—	—	4.0	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 10A, I_B = 100mA	—	—	3.5	V

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